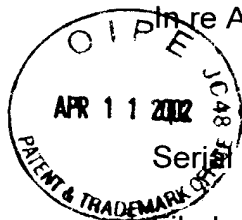


H6/H
la.
4/15/02
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



In re Application of:

KUO et al.

Serial No.: 09/839,365

Filed: April 23, 2001

Group Art Unit: 1765

Examiner: V. Perez-Ramos

For: METHOD FOR FORMING CONTACT WINDOW

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

RECEIVED

APR 15 2002

TC 1700

Sir:

This is in response to the Official Action of December 11, 2001, in connection with the above-identified application. The period for response to this Official Action has been extended to expire on April 11, 2002, by the filing herewith of a Petition for a one-month extension of time and payment of the required fee.

Please amend the above-identified application as follows.

IN THE SPECIFICATION:

On page 2, please replace the paragraph beginning at line 4 with the following amended paragraph.

No matter how, although width of contact window is decreased as integration is increased, thickness of contact window is still restricted in a finite range for heights of related semiconductor elements still are not negligible. For example, typical thickness of contact window of logic IC is about 1 micron. Nevertheless, for memory IC there are both gate and capacitor and then typical thickness of contact window is about 2 micron to 2.5 micron. Thus, aspect ratio is increased as scale of semiconductor element is minimized and then step coverage of filled material is degraded.